



AMENDMENTS TO THE CLAIMS:

This listing of claims replaces all prior versions and listings of claims in the application:

Listing of Claims:

Claim 1 (Currently Amended) A semiconductor device comprising:  
a semiconductor layer formed on an insulating surface, and having at least a source region, a drain region, and a channel formation region interposed therebetween;  
a first insulating film formed on said semiconductor layer;  
at least one electrode formed on said first insulating film, and overlapping said channel formation region;  
a source wiring formed on said first insulating film;  
a second insulating film covering at least said at least one electrode and said source wiring; and  
a gate wiring formed [[on]] in contact with said second insulating film, and connected to said at least one electrode.

Claim 2 (Original) A semiconductor device according to claim 1, wherein said gate wiring overlaps a portion of said semiconductor layer containing at least said channel formation region.

Claim 3 (Previously presented) A semiconductor device according to claim 1, wherein said at least one electrode comprises a gate electrode.

Claim 4 (Previously presented) A semiconductor device according to claim 1, wherein said at least one electrode and said source wiring comprise a same material.

Claim 5 (Original) A semiconductor device according to claim 1, wherein a material of said gate wiring comprises one or a plurality of elements selected from the group consisting of poly-Si, W, WSi<sub>x</sub>, Al, Cu, Ta, Cr and Mo.

Claim 6 (Original) A semiconductor device according to claim 1, wherein said first insulating film comprises a gate insulating film.

Claim 7 (Original) A semiconductor device according to claim 1, wherein said second insulating film further comprises a first insulating layer containing silicon as a main component and a second insulating layer containing an organic resin material.

Claim 8 (Previously presented) A semiconductor device according to claim 1, wherein said semiconductor device is one selected from the group consisting of a personal computer, a video camera, a portable information terminal, a digital camera, a digital video disk player, a portable telephone, an electronic book, a projector, a head mounted type display, and an electric game appliance.

Claim 9 (Currently Amended) A semiconductor device comprising:  
a semiconductor layer formed on an insulating surface, and having at least a source region, a drain region, and a channel formation region interposed therebetween;  
a first insulating film formed on said semiconductor layer;  
at least one electrode formed on said first insulating film, and overlapping said channel formation region;  
a source wiring formed on said first insulating film;  
a second insulating film covering at least said at least one electrode and said source wiring;  
a gate wiring formed **[[on]]** in contact with said second insulating film, and connected to said at least one electrode;

a connection electrode formed on said second insulating film, and connected to said source wiring and said semiconductor layer; and

a pixel electrode formed on said second insulating film, and electrically connected to said semiconductor layer.

Claim 10 (Original) A semiconductor device according to claim 9, wherein said pixel electrode overlaps said source wiring.

Claim 11 (Original) A semiconductor device according to claim 9, wherein said gate wiring overlaps a portion of said semiconductor layer containing at least said channel formation region.

Claim 12 (Previously presented) A semiconductor device according to claim 9, wherein said at least one electrode comprises a gate electrode.

Claim 13 (Previously presented) A semiconductor device according to claim 9, wherein said at least one electrode and said source wiring comprise a same material.

Claim 14 (Original) A semiconductor device according to claim 9, wherein said pixel electrode, said connection electrode and said gate wiring comprise a same material.

Claim 15 (Original) A semiconductor device according to claim 9, wherein a material of said gate wiring comprises one or a plurality of elements selected from the group consisting of poly-Si, W,  $WSi_x$ , Al, Cu, Ta, Cr and Mo.

Claim 16 (Original) A semiconductor device according to claim 9, wherein said first insulating film comprises a gate insulating film.

Claim 17 (Original) A semiconductor device according to claim 9, wherein said second insulating film further comprises a first insulating layer containing silicon as a main component and a second insulating layer containing an organic resin material.

Claim 18 (Previously presented) A semiconductor device according to claim 9, wherein one pixel including said pixel electrode forms a storage capacitor between said semiconductor layer connected to said pixel electrode and said at least one electrode connected to a gate wiring of an adjacent pixel, using said first insulating film as a dielectric.

Claim 19 (Original) A semiconductor device according to claim 9, wherein an impurity element for imparting a p-type conductivity is added to said semiconductor layer connected to said pixel electrode.

Claim 20 (Previously presented) A semiconductor device according to claim 9, said semiconductor device is one selected from the group consisting of a personal computer, a video camera, a portable information terminal, a digital camera, a digital video disk player, a portable telephone, an electronic book, a projector, a head mounted type display, and an electric game appliance.

Claim 21 (Currently Amended) A semiconductor device comprising:  
~~a first insulating film adjacent to a semiconductor layer, said semiconductor layer having at least a source region, a drain region, and a channel formation region interposed therebetween;~~  
~~at least one electrode including a gate electrode formed on said first insulating film;~~  
a semiconductor layer and at least one electrode including a gate electrode adjacent to said semiconductor layer with a first insulating film interposed therebetween;  
a source wiring formed on said first insulating film;  
a second insulating film covering at least said at least one electrode and said source wiring;

a gate wiring formed [[on]] in contact with said second insulating film, and electrically connected to said at least one electrode; and  
a pixel electrode electrically connected to said semiconductor layer,  
wherein ~~said gate wiring and~~ said pixel electrode [[are]] is formed on said second insulating film.

Claim 22 (Original) A semiconductor device according to claim 21, wherein said gate wiring overlaps a portion of said semiconductor layer containing at least said channel formation region.

Claim 23 (Previously presented) A semiconductor device according to claim 21, wherein said at least one electrode and said source wiring comprise a same material.

Claim 24 (Original) A semiconductor device according to claim 21, wherein a material of said gate wiring comprises one or a plurality of elements selected from the group consisting of poly-Si, W, WSi<sub>x</sub>, Al, Cu, Ta, Cr and Mo.

Claim 25 (Original) A semiconductor device according to claim 21, wherein said first insulating film comprises a gate insulating film.

Claim 26 (Original) A semiconductor device according to claim 21, wherein said second insulating film further comprises a first insulating layer containing silicon as a main component and a second insulating layer containing an organic resin material.

Claim 27 (Previously presented) A semiconductor device according to claim 21, wherein said semiconductor device is one selected from the group consisting of a personal computer, a video camera, a portable information terminal, a digital camera, a digital video disk player, a

portable telephone, an electronic book, a projector, a head mounted type display, and an electric game appliance.

Claim 28 (Previously presented) A semiconductor device comprising a pair of substrates and a liquid crystal interposed therebetween, one of said pair of substrates having at least a pixel portion and a driver circuit, said pixel portion comprising:

- a semiconductor layer formed on an insulating surface, and having at least a source region, a drain region and a channel formation region interposed therebetween;

- a first insulating film formed on said semiconductor layer;

- at least one electrode formed on said first insulating film, and overlapping at least said channel formation region;

- a source wiring formed on said first insulating film;

- a second insulating film covering at least said at least one electrode and said source wiring;

- a gate wiring formed on said second insulating film, and connected to said at least one electrode;

- a connection electrode formed on said second insulating film, and connected to said source wiring and said semiconductor layer; and

- a pixel electrode formed on said second insulating film, and electrically connected to said semiconductor layer, and

wherein another one of said pair of substrates comprises a light-shielding film in which a red color filter and a blue color filter are laminated so as to overlap said semiconductor layer.

Claim 29 (Original) A semiconductor device according to claim 28, further comprising a common wiring on said second insulating film, wherein said pixel electrode and said common wiring are arranged so that an electric field substantially parallel to a surface of said substrate is generated.

Claim 30 (Original) A semiconductor device according to claim 28, said semiconductor device is a reflection-type liquid crystal display device in which said pixel electrode comprises a film containing Al or Ag or a lamination film thereof.

Claim 31 (Original) A semiconductor device according to claim 28, said semiconductor device is a transmission-type liquid crystal display device in which said pixel electrode comprises a transparent electrically conductive film.

Claim 32 (Previously presented) A semiconductor device according to claim 28, said semiconductor device is one selected from the group consisting of a personal computer, a video camera, a portable information terminal, a digital camera, a digital video disk player, a portable telephone, an electronic book, a projector, a head mounted type display, and an electric game appliance.

Claim 33 (Previously presented) A semiconductor device comprising a pair of substrates and a liquid crystal interposed therebetween, one of said pair of substrates having at least a pixel portion and a driver circuit, said pixel portion comprising:

- a semiconductor layer formed on an insulating surface, and having at least a source region, a drain region and a channel formation region interposed therebetween;

- a first insulating film formed on said semiconductor layer;

- at least one electrode formed on said first insulating film, and overlapping at least said channel formation region;

- a source wiring formed on said first insulating film;

- a second insulating film covering at least said at least one electrode and said source wiring;

- a gate wiring formed on said second insulating film, and connected to said at least one electrode; and

a pixel electrode formed on said second insulating film, and electrically connected to said semiconductor layer.

Claim 34 (Original) A semiconductor device according to claim 33, further comprising a common wiring on said second insulating film, wherein said pixel electrode and said common wiring are arranged so that an electric field substantially parallel to a surface of said substrate is generated.

Claim 35 (Original) A semiconductor device according to claim 33, said semiconductor device is a reflection-type liquid crystal display device in which said pixel electrode comprises a film containing Al or Ag or a lamination film thereof.

Claim 36 (Original) A semiconductor device according to claim 33, said semiconductor device is a transmission-type liquid crystal display device in which said pixel electrode comprises a transparent electrically conductive film.

Claim 37 (Previously presented) A semiconductor device according to claim 33, said semiconductor device is one selected from the group consisting of a personal computer, a video camera, a portable information terminal, a digital camera, a digital video disk player, a portable telephone, an electronic book, a projector, a head mounted type display, and an electric game appliance.

Claims 38-44 (canceled)

Claim 45 (New) A semiconductor device comprising:  
a semiconductor layer and at least one electrode adjacent to said semiconductor layer with a first insulating film interposed therebetween;  
a source wiring formed on said first insulating film;



a second insulating film covering at least said at least one electrode and said source wiring; and

a gate wiring formed in contact with said second insulating film, and electrically connected to said at least one electrode.

46. (New) A semiconductor device according to claim 45, wherein said gate wiring overlaps a portion of said semiconductor layer containing at least a channel formation region.

47. (New) A semiconductor device according to claim 45, wherein said at least one electrode and said source wiring comprise a same material.

48. (New) A semiconductor device according to claim 45, wherein a material of said gate wiring comprises one or a plurality of elements selected from the group consisting of poly-Si, W, WSi<sub>x</sub>, Al, Cu, Ta, Cr and Mo.

49. (New) A semiconductor device according to claim 45, wherein said first insulating film comprises a gate insulating film.

50. (New) A semiconductor device according to claim 45, wherein said second insulating film further comprises a first insulating layer containing silicon as a main component and a second insulating layer containing an organic resin material.

51. (New) A semiconductor device according to claim 45, wherein said semiconductor device is one selected from the group consisting of a personal computer, a video camera, a portable information terminal, a digital camera, a digital video disk player, a portable telephone, an electronic book, a projector, a head mounted type display, and an electric game appliance.